

Silicon PNP Power Transistors

2N4898 2N4899 2N4900

DESCRIPTION

- With TO-66 package
- Low collector saturation voltage
- Excellent safe operating area
- 2N4900 complement to type 2N4912

APPLICATIONS

- Designed for driver circuits,switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

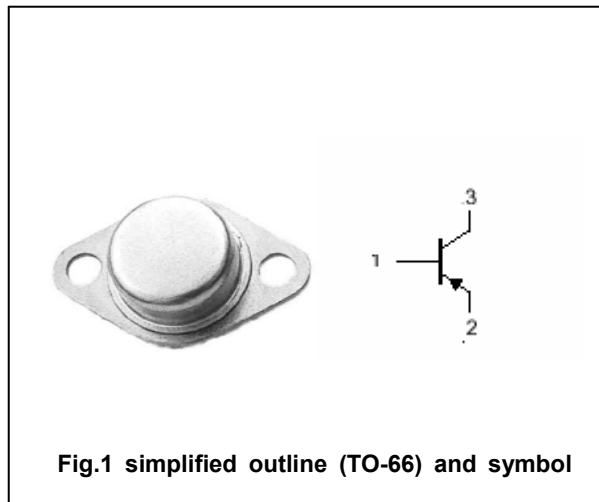


Fig.1 simplified outline (TO-66) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N4898	-40	V
		2N4899	-60	
		2N4900	-80	
V _{CEO}	Collector-emitter voltage	2N4898	-40	V
		2N4899	-60	
		2N4900	-80	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-1.0	A
I _{CM}	Collector current-peak		-4.0	A
I _B	Base current		-1.0	A
P _D	Total Power Dissipation	T _C =25°C	25	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{(th) jc}	Thermal resistance junction to case	7.0	°C/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N4898	-40			V	
		2N4899	-60				
		2N4900	-80				
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-0.6	V	
V _{BE(sat)}	Base-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-1.3	V	
V _{BE(on)}	Base-emitter on voltage	I _C =-1A; V _{CE} =-1V			-1.3	V	
I _{CEO}	Collector cut-off current	2N4898	V _{CE} =-20V; I _B =0			-0.5	mA
		2N4899	V _{CE} =-30V; I _B =0				
		2N4900	V _{CE} =-40V; I _B =0				
I _{CEX}	Collector cut-off current	V _{CE} =Rated V _{CEO} ; V _{BE(off)} =1.5V T _C =150°C			-0.1 -1.0	mA	
I _{CBO}	Collector cut-off current	V _{CB} =Rated V _{CBO} ; I _E =0			-0.1	mA	
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1.0	mA	
h _{FE-1}	DC current gain	I _C =-50mA; V _{CE} =-1V	40				
h _{FE-2}	DC current gain	I _C =-500mA; V _{CE} =-1V	20		100		
h _{FE-3}	DC current gain	I _C =-1.0A; V _{CE} =-1V	10				
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz			100	pF	
f _T	Transition frequency	I _C =-250mA; V _{CE} =-10V	3.0			MHz	

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PACKAGE OUTLINE



Fig.2 outline dimensions